

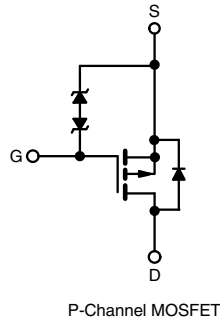
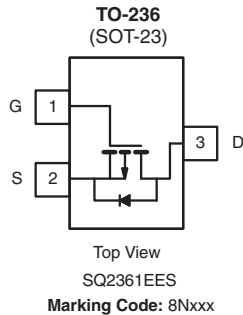
Automotive P-Channel 60 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY	
V_{DS} (V)	- 60
$R_{DS(on)}$ (Ω) at $V_{GS} = -10$ V	0.150
$R_{DS(on)}$ (Ω) at $V_{GS} = -4.5$ V	0.200
I_D (A)	- 2.5

FEATURES

- TrenchFET® Power MOSFET
- Typical ESD Protection: 800 V
- AEC-Q101 Qualified
- 100 % R_g and UIS Tested
- Material categorization:
For definitions of compliance please see www.vishay.com/doc?99912



ORDERING INFORMATION	
Package	SOT-23
Lead (Pb)-free and Halogen-free	SQ2361EES-T1-GE3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	- 60	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	$T_C = 25$ °C	- 2.5
		$T_C = 125$ °C	- 1.4
Continuous Source Current (Diode Conduction)	I_S	- 2.5	A
Pulsed Drain Current ^a	I_{DM}	- 10	
Single Pulse Avalanche Current	I_{AS}	- 15	
Single Pulse Avalanche Energy	E_{AS}	11	mJ
Maximum Power Dissipation ^a			
		$T_C = 125$ °C	0.67
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient	R_{thJA}	175	°C/W
Junction-to-Foot (Drain)			

Notes

- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR-4 material).



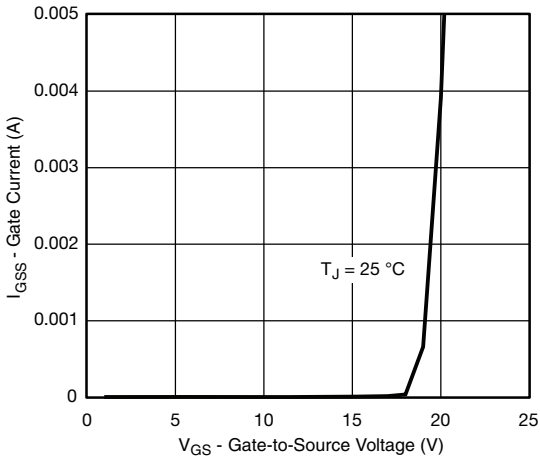
SPECIFICATIONS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = -250\text{ }\mu\text{A}$	-60	-	-	V
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250\text{ }\mu\text{A}$	-1.5	-	-2.5	
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 20\text{ V}$	-	-	± 30	mA
		$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 8\text{ V}$	-	-	± 2	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}$, $V_{DS} = -60\text{ V}$	-	-	-1	μA
		$V_{GS} = 0\text{ V}$, $V_{DS} = -60\text{ V}$, $T_J = 125\text{ }^\circ\text{C}$	-	-	-50	
		$V_{GS} = 0\text{ V}$, $V_{DS} = -60\text{ V}$, $T_J = 175\text{ }^\circ\text{C}$	-	-	-150	
On-State Drain Current ^a	$I_{D(on)}$	$V_{GS} = -10\text{ V}$, $V_{DS} \leq -5\text{ V}$	-10	-	-	A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -10\text{ V}$, $I_D = -2.4\text{ A}$	-	0.115	0.150	Ω
		$V_{GS} = -10\text{ V}$, $I_D = -2.4\text{ A}$, $T_J = 125\text{ }^\circ\text{C}$	-	-	0.260	
		$V_{GS} = -10\text{ V}$, $I_D = -2.4\text{ A}$, $T_J = 175\text{ }^\circ\text{C}$	-	-	0.310	
		$V_{GS} = -4.5\text{ V}$, $I_D = -1.8\text{ A}$	-	0.160	0.200	
Forward Transconductance ^b	g_{fs}	$V_{DS} = -10\text{ V}$, $I_D = -2\text{ A}$	-	5	-	S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = -30\text{ V}$, $f = 1\text{ MHz}$	-	435	545	μF
Output Capacitance	C_{oss}		-	55	70	
Reverse Transfer Capacitance	C_{rss}		-	40	50	
Total Gate Charge ^c	Q_g	$V_{GS} = -10\text{ V}$, $V_{DS} = -30\text{ V}$, $I_D = -6\text{ A}$	-	11.2	17	nC
Gate-Source Charge ^c	Q_{gs}		-	1.6	-	
Gate-Drain Charge ^c	Q_{gd}		-	3.2	-	
Gate Resistance	R_g	$f = 1\text{ MHz}$	2.7	5.4	8.1	Ω
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = -30\text{ V}$, $R_L = 20\text{ }\Omega$ $I_D \cong -1.5\text{ A}$, $V_{GEN} = -10\text{ V}$, $R_g = 1\text{ }\Omega$	-	7	11	ns
Rise Time ^c	t_r		-	8	12	
Turn-Off Delay Time ^c	$t_{d(off)}$		-	19	29	
Fall Time ^c	t_f		-	8	12	
Source-Drain Diode Ratings and Characteristics^b						
Pulsed Current ^a	I_{SM}		-	-	-10	A
Forward Voltage	V_{SD}	$I_F = -1.5\text{ A}$, $V_{GS} = 0\text{ V}$	-	-0.8	-1.2	V

Notes

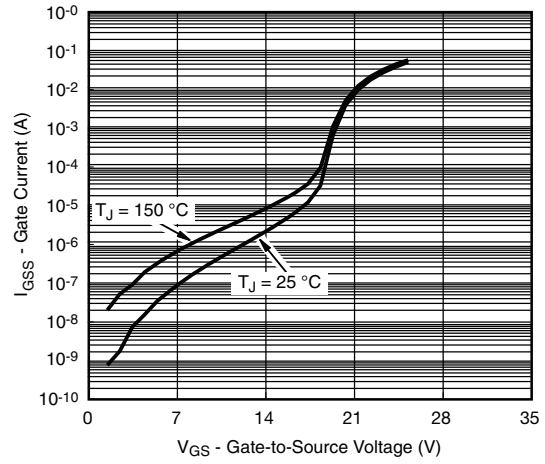
- Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

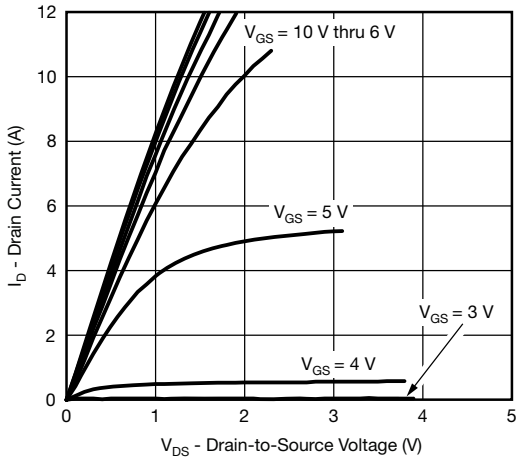
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



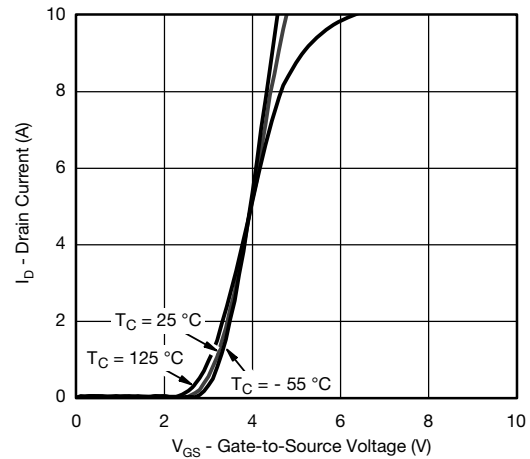
Gate Current vs. Gate-Source Voltage



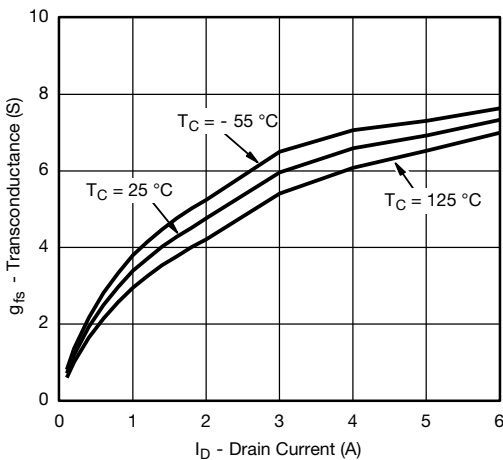
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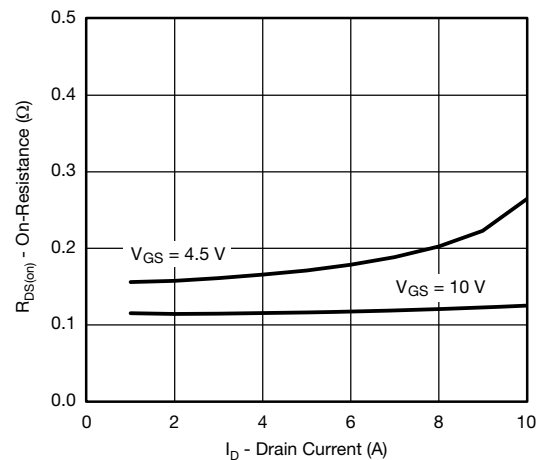
Output Characteristics



Transfer Characteristics

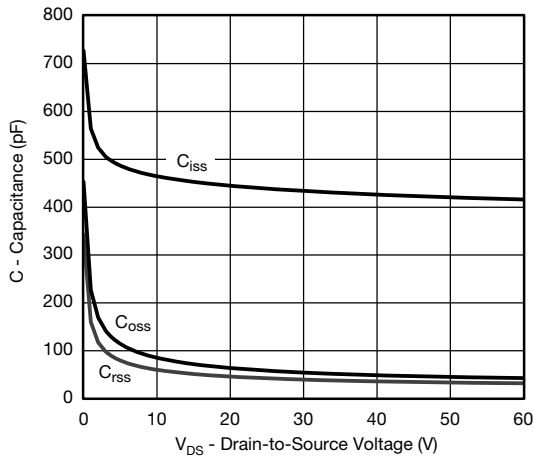


Transconductance

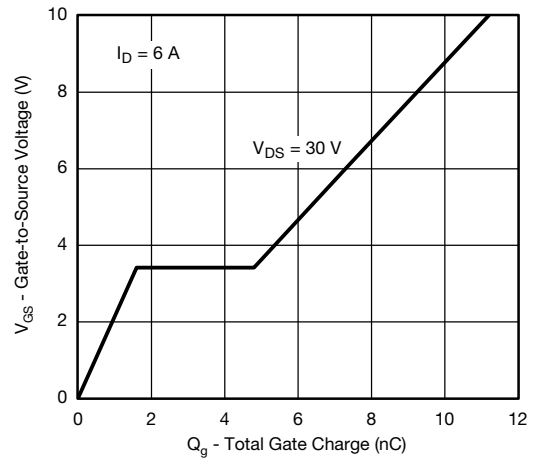


On-Resistance vs. Drain Current

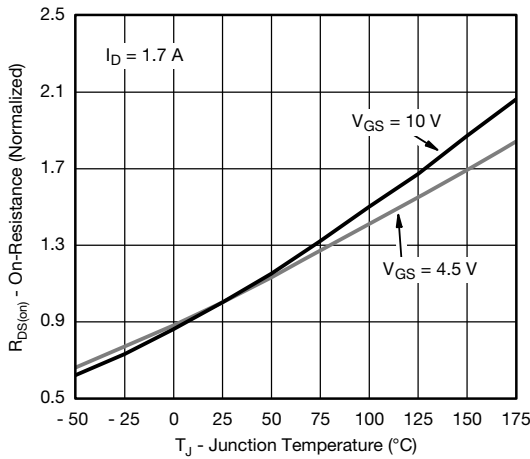
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



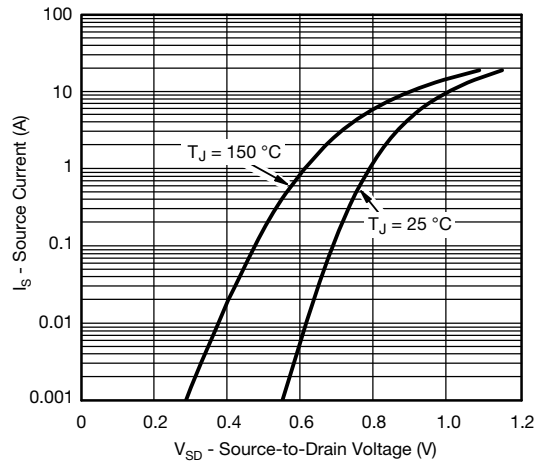
Capacitance



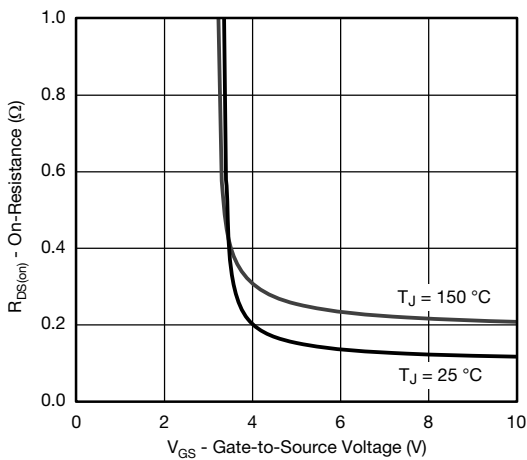
Gate Charge



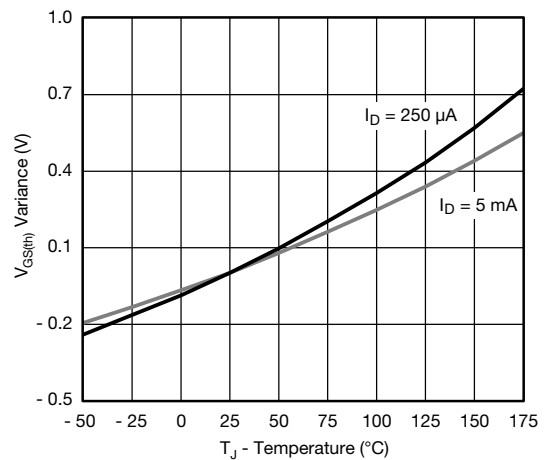
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage



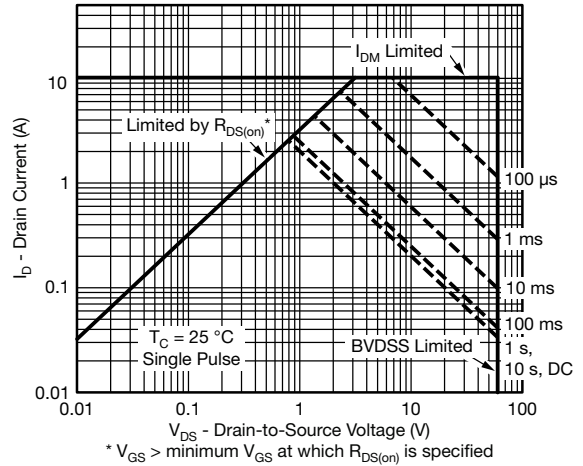
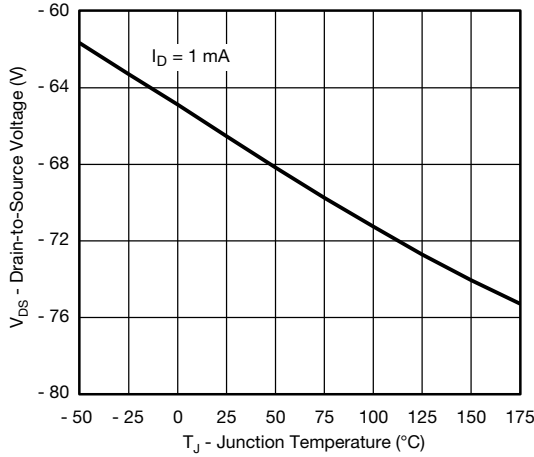
On-Resistance vs. Gate-Source Voltage



Threshold Voltage

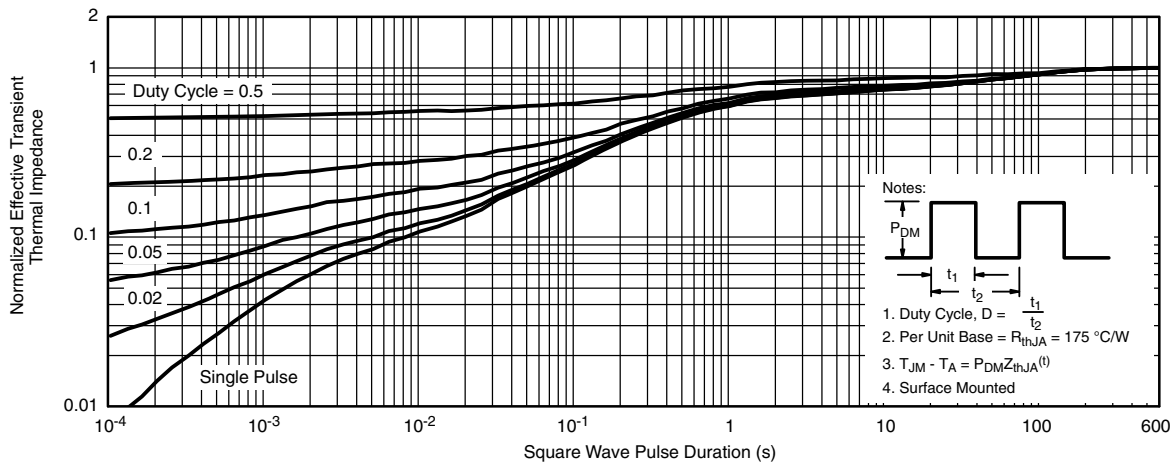


THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Drain Source Breakdown vs. Junction Temperature

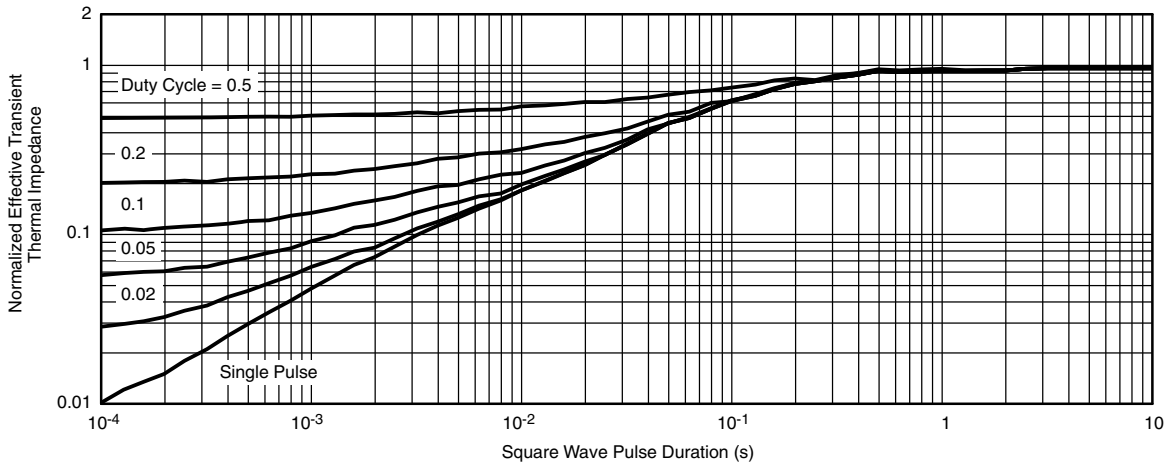
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^\circ\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Foot ($25\text{ }^\circ\text{C}$)
 are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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